

ABSTRACT

A semiconductor device has

a circuit board,

a ferroelectric capacitor arranged on said circuit board, having a ferroelectric thin film and top and bottom electrodes which are formed so as to hold said ferroelectric thin film,

an insulating film formed on said circuit board so as to cover said ferroelectric capacitor,

a metallic wiring film formed on said insulating film so as to connect with either of said top and bottom electrodes, and

a surface protective film formed so as to cover said insulating film and said metallic wiring film, wherein

a synthetic stress working in a surface direction of the ferroelectric thin film of said ferroelectric capacitor is an extensional stress.